Electronic Properties of Solids R.J. Nicholas

Electronic Properties:

- Metals
- Semiconductors
- Insulators
- Paramagnets
- Diamagnets
- Ferromagnets
- Superconductors

Combination of:

Crystal Structure

Atomic Structure

Free electron theory of metals

- Metals are good conductors (both electrical and thermal)
- Electronic heat capacity has an additional (temperature dependent) contribution from the electrons.
- Why are some materials metals and others not?

Simple approximation: treat electrons as free to move within the crystal

Free electron theory of metals

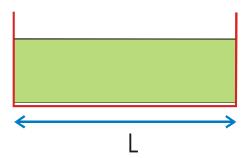
- Alkali metals (K, Na, Rb) and Noble metals (Cu, Ag,
 Au) have filled shell + 1 outer s-electron.
- Atomic s-electrons are *delocalised* due to overlap of outer orbits.
- Crystal looks like positive ion cores of charge +e
 embedded in a sea of conduction electrons
- Conduction electrons can interact with each other and ion cores but these interactions are weak because:

- (1) Periodic crystal potential (ion cores) is orthogonal to conduction electrons they are eigenstates of total Hamiltonian e.g. for Na conduct. electrons are 3s states, but cores are n=1 and n=2 atomic orbitals.
- (2) Electron-electron scattering is suppressed by Pauli exclusion principle.

Assumptions:

- (i) ions are static adiabatic approx.
- (ii) electrons are independent do not interact.
- (iii) model interactions with ion cores by using an "effective mass" m*
- (iv) free electrons so we usually put $m^* = m_a$

Free Electron Model



Put free electrons into a very wide potential well the same size as the crystal i.e. they are 'de-localised'

Free electron properties

Free electron Hamiltonian has only kinetic energy operator:

$$E\psi = -\frac{\hbar^2}{2m}\frac{\partial^2\psi}{\partial x^2}$$

Free electrons are plane waves

$$\psi = A e^{\pm ikx}$$

with:

Momentum:

Energy:

Group velocity:

$$i\hbar\frac{\partial\psi}{\partial x} = \pm\hbar k\,\psi$$

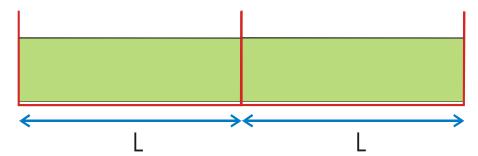
$$i\hbar \frac{\partial \psi}{\partial x} = \pm \hbar k \psi$$

$$-\frac{\hbar^2}{2m} \frac{\partial^2 \psi}{\partial x^2} = \frac{\hbar^2 k^2}{2m} \psi$$

$$\frac{\partial \omega}{\partial k} = \frac{1}{\hbar} \frac{\partial E}{\partial k} = \frac{\hbar k}{m}$$

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Free Electron Model – Periodic boundary conditions



Add a second piece of crystal the same size:

The properties must be the same.

Density of states

Calculate allowed values of k.

Use periodic (Born-von Karman) boundary conditions:

$$\psi(x) = \psi(x+L)$$

$$\therefore e^{ikx} = e^{ik(x+L)}$$

$$\therefore e^{ikL} = 1$$

L = size of crystal

$$\therefore k = 0, \pm \frac{2\pi}{L}, \pm \frac{4\pi}{L}$$

$$\therefore \delta k = \frac{2\pi}{L}$$

Density of allowed states in reciprocal (k-) space is:

$$\frac{\Delta K}{\delta k}$$
 in $1-D$ or $\frac{\Delta V_K}{\delta k^3}$ in $3-D$ x 2 for spin states

Density of states (2)

States have energies ε to ε + d ε

$$g(\varepsilon)d\varepsilon = g(k)dk = 4\pi k^2 dk \times \frac{2}{\delta k^3}$$

$$\varepsilon = \frac{\hbar^2 k^2}{2m}$$

$$k = \left(\frac{2m\varepsilon}{\hbar^2}\right)^{1/2}$$

$$\frac{dk}{d\varepsilon} = \left(\frac{2m}{\hbar^2}\right)^{1/2} \frac{1}{2\varepsilon^{1/2}}$$

$$\therefore g(\varepsilon) d\varepsilon = g(k) \frac{dk}{d\varepsilon} d\varepsilon$$

$$= \frac{8\pi}{\left(\frac{2\pi}{L}\right)^3} k^2 \left(\frac{2m}{\hbar^2}\right)^{\frac{1}{2}} \frac{1}{2\varepsilon^{\frac{1}{2}}} d\varepsilon$$

$$= \frac{4\pi}{\left(\frac{2\pi}{L}\right)^3} \frac{2m\varepsilon}{\hbar^2} \left(\frac{2m}{\hbar^2}\right)^{\frac{1}{2}} \frac{1}{\varepsilon^{\frac{1}{2}}} d\varepsilon$$

$$= 4\pi \left(\frac{2m}{\hbar^2}\right)^{\frac{3}{2}} \varepsilon^{\frac{1}{2}} d\varepsilon \times V$$

Fermi Energy

Electrons are Fermions
$$N = \int_0^\infty g(\varepsilon) f_{F-D}(\varepsilon) d\varepsilon$$

$$at T = 0 \qquad N = \int_0^\mu g(\varepsilon) d\varepsilon$$

$$n = \frac{N}{V} = \frac{8\pi}{3} \left(\frac{2mE_F}{h^2}\right)^{\frac{3}{2}}$$
 μ at T = 0 is known as the Fermi Energy, E_F
$$E_F = \left(\frac{3N}{8\pi V}\right)^{\frac{2}{3}} \frac{h^2}{2m}$$

Typical value for E_F e.g. Sodium (monatomic)

crystal structure: b.c.c. crystal basis: single Na atom lattice points per conventional (cubic) unit cell: 2 conduction electrons per unit cell 2

∴ electrons per lattice point = 1

lattice constant (cube side) = a = 0.423 nm \therefore density of electrons $n = N/V = 2/a^3 = 2.6 \times 10^{28} \, \text{m}^{-3}$ $\therefore E_F = 3.2 \, \text{eV}$

Fermi Temperature T_F ? $k_B T_F = E_F$ $\therefore T_F = 24,000 \text{ K}$

Finite Temperatures and Heat Capacity

Fermi-Dirac distribution function $f_{F-D} = 1/(e^{E-\mu/k_BT}+1)$ electrons are excited by an energy $\sim k_BT$

Number of electrons is $\approx k_B T g(E_F)$

$$\therefore \Delta E \approx k_B^2 T^2 g(E_F)$$

$$\therefore$$
 C_V = Δ E/ Δ T $\approx 2k_B^2$ T g(E_F)

Previously
$$\therefore \ln n = \frac{3}{2} \ln E + const.$$
we have $n = AE_F^{3/2}$

$$\therefore \frac{dn}{n} = \frac{3}{2} \frac{dE}{E}$$

$$\frac{dn}{dE} = \frac{3}{2} \frac{n}{E_F} = g(E_F)$$

$$\therefore C_v = 3nk_B \frac{k_BT}{E_F} = 3nk_B \frac{T}{T_F}$$

- :. Heat Capacity is:
- (i) less than classical value by factor $\sim k_B T/E_F$
- (ii) proportional to g(E_F)

Is this significant?

	Lattice	Electrons	
Room Temperature	$3n_{at.}k_{B}$	$\pi^2/2 \text{ nk}_{\text{B}} \left(\text{k}_{\text{B}} \text{T/E}_{\text{F}} \right)$	
Low Temperature	$12\pi^4/5 \; n_{at.} k_B \; (T/\Theta_D)^3$	$\pi^2/2 \text{ nk}_{\text{B}} \left(\text{k}_{\text{B}} \text{T}/\text{E}_{\text{F}} \right)$	
	$C/T = \beta T^2 + \gamma$ Debye term free electron term		

Rigorous derivation

$$U = \int_{0}^{\infty} \varepsilon \ g(\varepsilon) \ f_{F-D}(\varepsilon) \ d\varepsilon$$

$$\therefore \frac{\partial U}{\partial T} = \int_{0}^{\infty} \varepsilon \ g(\varepsilon) \frac{\partial f}{\partial T} \ d\varepsilon$$

$$= g(E_F) \ k_B^2 T \int_{\frac{-E_F}{k_B T}}^{\infty} \frac{x^2 e^x dx}{\left(e^x + 1\right)^2} + \delta$$

$$= \frac{\pi^2}{3} \ g(E_F) \ k_B^2 T \approx -\infty$$

$$\int_{-E_F}^{\infty} \frac{x e^x dx}{\left(e^x + 1\right)^2} d\varepsilon$$

$$= -\infty$$

$$\delta \propto \int_{\frac{-E_F}{k_B T}}^{\infty} \frac{x e^x dx}{\left(e^x + 1\right)^2}$$

$$= 0 \text{ (why?)}$$

Magnetic susceptibility

• Susceptibility for a spin ½ particle is:

$$\chi = \frac{\mu_B^2 \mu_0}{kT} / \text{electron}$$

- This is much bigger than is found experimentally
 - Why?

Pauli paramagnetism

Separate density of states for spin up and spin down, shifted in energy by $\pm \frac{1}{2}g\mu_B B$ (g=2)

Imbalance of electron moments Δn

$$\Delta n = \frac{1}{2} g(\epsilon_F) \times 2\mu_B B$$

giving a magnetization M

$$M = \mu_B \Delta n = \mu_B^2 g(\epsilon_F) B$$

and a susceptibility

$$\chi = M/H = \mu_0 \ \mu_B^2 \ g(\epsilon_F) = 3n\mu_0 \ \mu_B^2 \ /2\epsilon_F$$

k-space picture and the Fermi Surface

$$T=0$$
 states filled up to E_F

$$\therefore \frac{\hbar^2 k^2}{2m} = E_F$$

Map of filled states in k-space

= Fermi surface

$$\therefore k_F = \sqrt{\frac{2mE_F}{\hbar^2}}$$

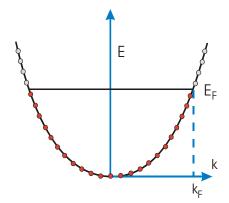
or we can write:

$$N = 2 \times \frac{4\pi}{3} \frac{k_F^3}{\left(\frac{2\pi}{L}\right)^3}$$

$$\therefore k_F^3 = \frac{3\pi^2 N}{V}$$

k-space picture and the Fermi Surface

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$$\therefore \frac{\hbar^2 k^2}{2m} = E_F$$

$$\therefore k_F = \sqrt{\frac{2mE_F}{\hbar^2}}$$

How big is Fermi surface/sphere compared to Brillouin Zone?

Simple cubic structure

volume of Brillouin Zone = $(2\pi/a)^3$

electron density $n = 1/a^3$

volume of Fermi sphere = $4\pi k_F^3/3 = 4\pi^3/a^3$

= half of one B.Z.

Electron Transport - Electrical Conductivity

Equation of motion: Force = rate of change of momentum

$$\hbar \frac{\partial k}{\partial t} = -e \left(\mathbf{E} + \mathbf{B} \times \mathbf{v} \right)$$

Apply electric field - electrons are accelerated to a steady state with a drift velocity v_d - momentum is lost by scattering with an average momentum relaxation time τ

$$\therefore \text{ momentum loss} = \frac{mv_d}{\tau} = -eE$$

$$\therefore \text{ current } j = nev_d = \frac{ne^2\tau}{m} E$$

$$\therefore \text{ conductivity } \sigma = \frac{ne^2\tau}{m} = ne\mu \qquad \mu \text{ is mobility with:}$$

$$\therefore \text{ conductivity } \sigma = \frac{ne^2\tau}{m} = ne\mu \qquad v_d = \mu E$$

$$v_d = \mu E$$

What happens in k-space?

All electrons in k-space are

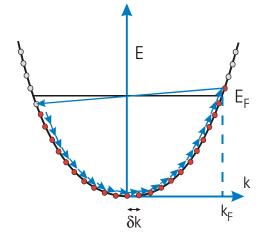
accelerated by electric field:

$$\hbar \, \delta k = F \, \delta t = -e E \, \delta t$$

On average all electrons

shifted by:

$$\delta k = -\frac{eE\tau}{\hbar}$$



What happens in k-space?

All electrons in k-space are accelerated by electric field:

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On average all electrons shifted by:

$$\delta k = -\frac{eE\tau}{\hbar}$$

Fermi sphere is shifted in k-space by $\delta k \ll k_E$

 $\mathrel{\raisebox{.3ex}{.}{:}}$ To relax electron momentum k must be changed by $\sim k_F$

Scattering occurs at E_F

:. we need phonons with large value of k. But phonon energy is small so only a small fraction of electrons $k_B T / \epsilon_F$ can be scattered

Scattering processes

Basic Principle: Scattering occurs because of deviations from perfect crystal arrangement

Electron scattering mechanisms:

- (i) thermal vibrations i.e. phonons (vibrations of the atoms are a deviation from perfect crystal structure)
- (ii) presence of impurities charged impurities are very important - scattering is by Coulomb force i.e.Rutherford scattering.

Matthiessen's rule: Scattering rates $(1/\tau)$ add

$$\therefore \rho = \frac{m}{ne^2} \sum_{\tau} \frac{1}{\tau} = \rho_{\tau} + \rho_{\tau}$$

Mean free path (λ) :

electrons are moving with Fermi velocity v_F

$$\therefore \quad \lambda = v_F \tau \ (NOT \ v_d \tau)$$

Low temperature mean free paths can be <u>very</u> long as electrons are only scattered by impurities

Hall Effect

In a magnetic Field **B** the electron experiences a force perpendicular to its velocity.

A current **j** causes a build up of charge at the edges which generates an Electric field **E** which balances the Lorentz force

$$(-e) (\mathbf{E} + \mathbf{v}_d \times \mathbf{B})_y = 0; \quad E_y = (v_d)_x B_z$$

Hall Effect

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A current **j** causes a build up of charge at the edges which generates an Electric field **E** which balances the Lorentz force

Balance of forces:

$$(-e) (\mathbf{E} + \mathbf{v}_d \times \mathbf{B})_y = 0; \quad E_y = (v_d)_x B_z$$

The Hall coefficient R_H is: $R_H = \frac{E_y}{j_x B_z}$

$$j_x = n(-e) v_d \implies R_H = -\frac{1}{ne}$$

Negative sign is sign of the charge on the electron

Metal	Charge/Atom (units of electron charge e)		Group
	Hall Expt.	FE Theory	
Lithium	-0.79	-1	I
Sodium	-1.13	-1	I
Potassium	-1.05	-1	I
Copper	-1.36	-1	IB
Silver	-1.18	-1	IB
Gold	-1.47	-1	IB
Beryllium	+0.1	-2	II
Magnesium	-0.88	-2	II
Calcium	-0.76	-2	II
Zinc	+0.75	-2	IIB
Cadmium	+1.2	-2	IIB
Aluminium	+1.0	-3	III
Indium	+1.0	-3	III

Thermal conductivity

In metals heat is mainly carried by the electrons Simple kinetic theory formula for thermal conductivity K:

$$\begin{split} K &= {}^{1}\!/_{3}C\lambda v_{F} & [C &= \pi^{2}\!/3 \ k_{B}{}^{2}T \ g(E_{F}) &= \pi^{2}\!/2 \ nk_{B} \, k_{B}T/E_{F}] \\ &= \pi^{2}\!/6 \ \lambda v_{F} \ nk_{B} \, k_{B}T/E_{F} & [\lambda &= v_{F}\tau \ ; \quad E_{F} = {}^{1}\!/_{2}mv_{F}{}^{2}] \\ &= \pi^{2}\!/3m \ n \, k_{B}{}^{2}\tau \, T \end{split}$$

Scattering processes

- Low temperatures: defects, τ independent of T
- Intermediate temp. : Low Temp phonons Debye model $\tau \propto T^{\text{-}3}$
- High temperatures: 'classical' phonons $\tau \propto T^{-1}$

Wiedeman-Franz ratio

Electrical and Thermal conductivities of electrons are both proportional to the relaxation time τ

Taking the ratio of the two should make this cancel so if we define the Lorenz number as $L = K/(\sigma T)$ we have the

Wiedeman-Franz Law:
$$L = \frac{K}{\sigma} T = \frac{\pi^2 k_B^2}{3e^2}$$

Predicted value is absolute and the same for all metals.

Works well at high and low temps, - breaks down in 'Debye' region where energy and charge scattering are different

Successes and Failures of Free Electron Model

Successes:

- Temperature dependence of Heat Capacity
- paramagnetic (Pauli) susceptibility
- Ratio of thermal and electrical conductivities (Lorentz number)
- Magnitudes of heat capacities and Hall effect in simple metals

Failures:

- Heat capacities and Hall effect of many metals are wrong
- Hall effect can be **positive**
- Does not explain why mean free paths can be so long
- Does not explain why some materials are metals, some insulators and some are semiconductors

Nearly Free Electron Approximation

Use a travelling wavefunction for an electron, e^{ikx} , with kinetic energy $\hbar^2 k^2/2m$

Assume that this is <u>Bragg scattered</u> by the wavevector $G=2\pi/a$ to give a second wave $e^{i(k-G)x}$ with energy $\hbar^2(k-G)^2/2m$

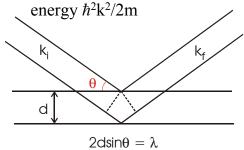
Crystal potential is periodic in real space. Therefore we can Fourier Transform the potential so that:

$$V(x) = \sum_{G} V_{G} \exp(iGx)$$

For a schematic solution we calculate what happens for a single Fourier component V_G so $V(x) = V_G(e^{iGx} + e^{-iGx})$

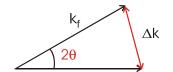
Nearly Free Electron Approximation

Use a travelling wavefunction for an electron, e ikx, with kinetic



Bragg scattering

$$\Delta \mathbf{k} = 2|\mathbf{k}|\sin\theta$$
$$= 4\pi/\lambda \sin\theta = 2\pi/d$$



$$\Delta \mathbf{k} = \mathbf{G} = \mathbf{h}\mathbf{a}^* + \mathbf{k}\mathbf{b}^* + \mathbf{l}\mathbf{c}^*$$

With d =
$$\frac{a}{\sqrt{h^2 + k^2 + l^2}}$$

Formally what we are doing is to solve the Hamiltonian form of Schrödinger equation

$$\mathbf{H} \boldsymbol{\psi} = \mathbf{E} \boldsymbol{\psi}$$

where ψ are the two travelling wave solutions. Expanding gives:

$$\begin{pmatrix} H_{11} - \lambda & H_{12} \\ H_{21} & H_{22} - \lambda \end{pmatrix} \begin{pmatrix} e^{ikx} \\ e^{i(k-G)x} \end{pmatrix} = (E - \lambda) \begin{pmatrix} e^{ikx} \\ e^{i(k-G)x} \end{pmatrix}$$

$$H_{11} = \left\langle \psi_1^* \middle| -\frac{\hbar^2}{2m} \frac{\partial^2}{\partial x^2} \middle| \psi_1 \right\rangle = \frac{\hbar^2 k^2}{2m}, \quad H_{22} = \frac{\hbar^2 (k - G)^2}{2m}$$

$$H_{12} = \left\langle \psi_1^* \middle| V(x) \middle| \psi_2 \right\rangle = V_G$$

$$H_{12} = \left\langle \psi_1 * \middle| V(x) \middle| \psi_2 \right\rangle = V_G$$